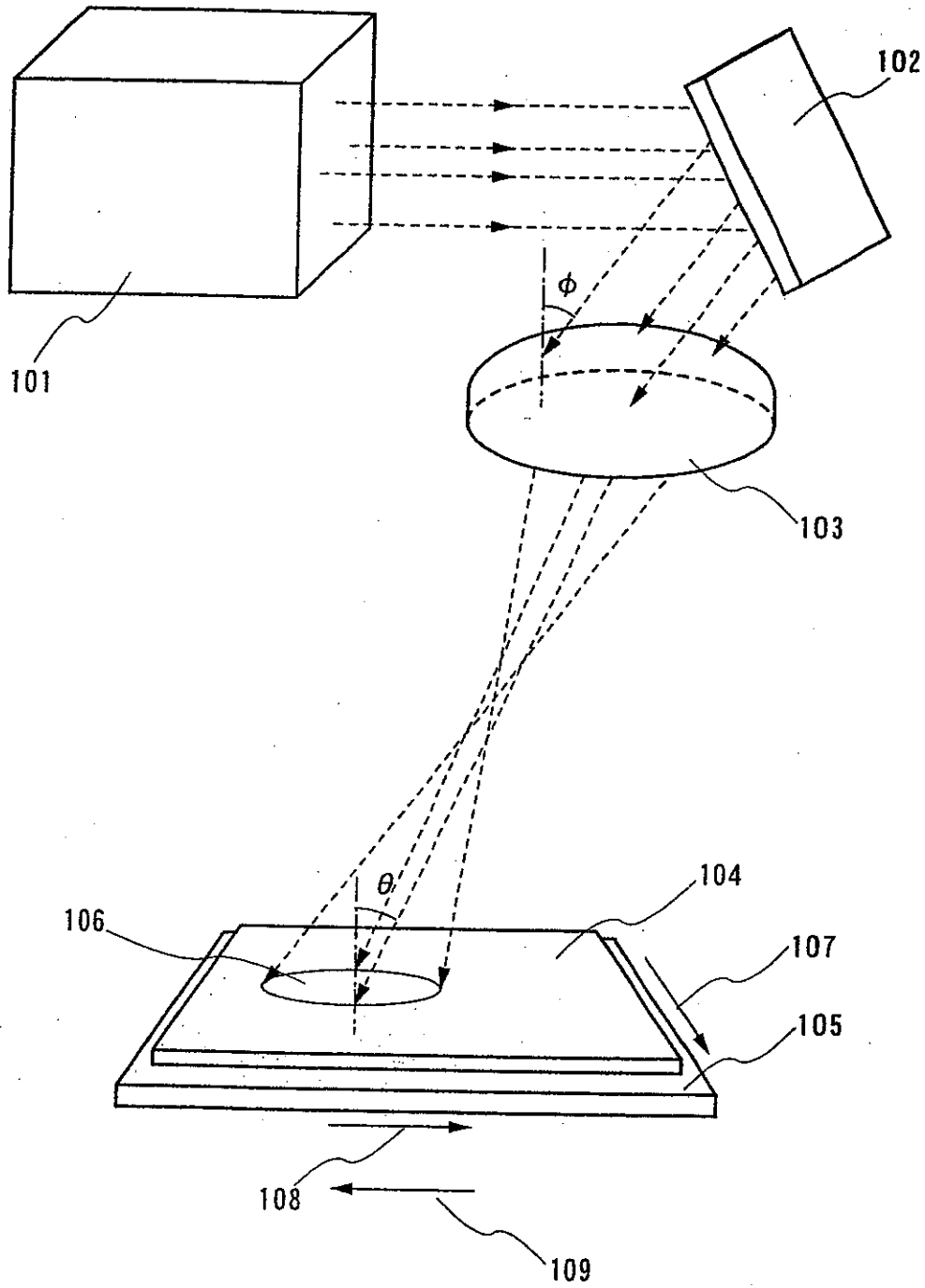


Fig. 1



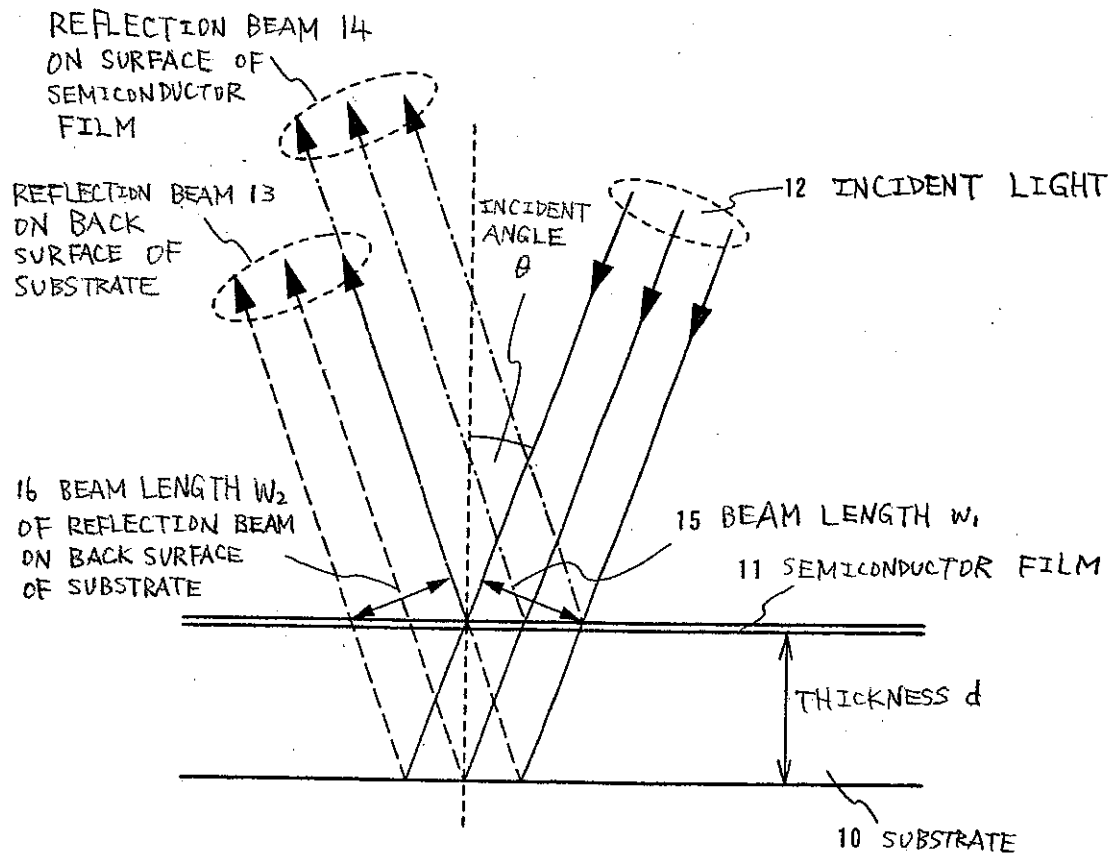


Fig.2

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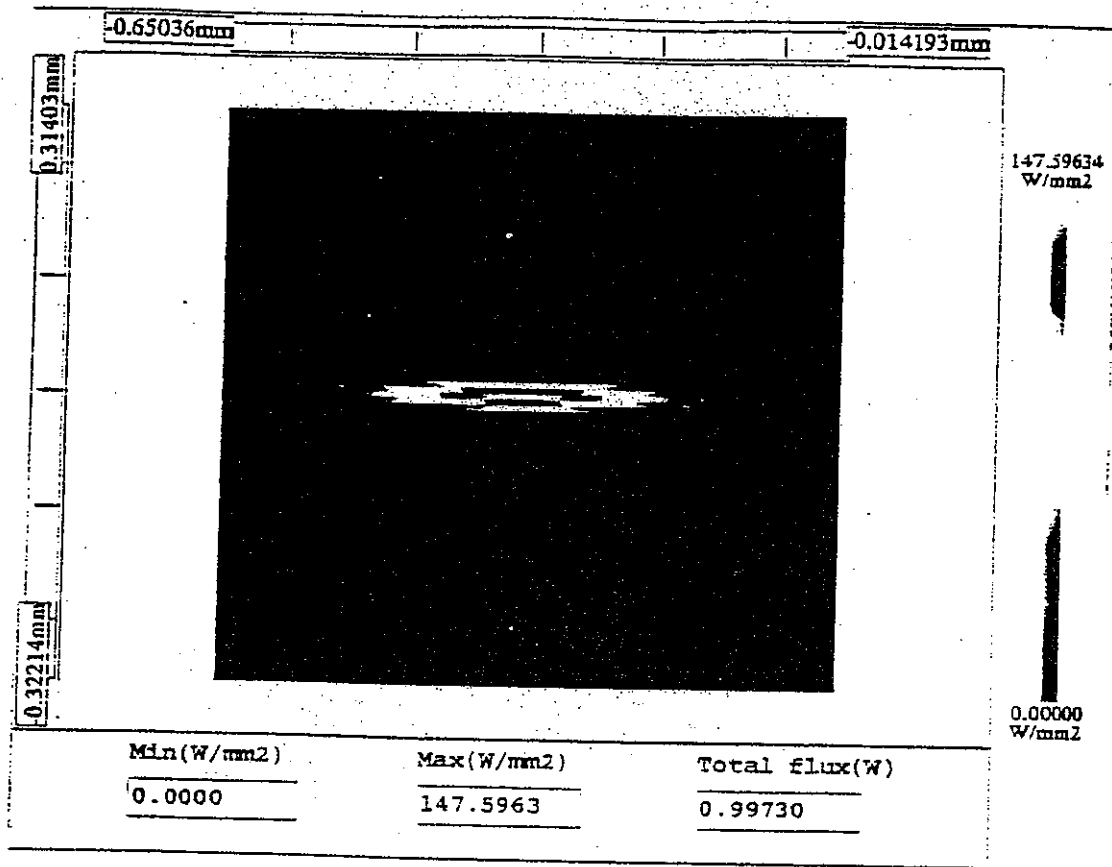
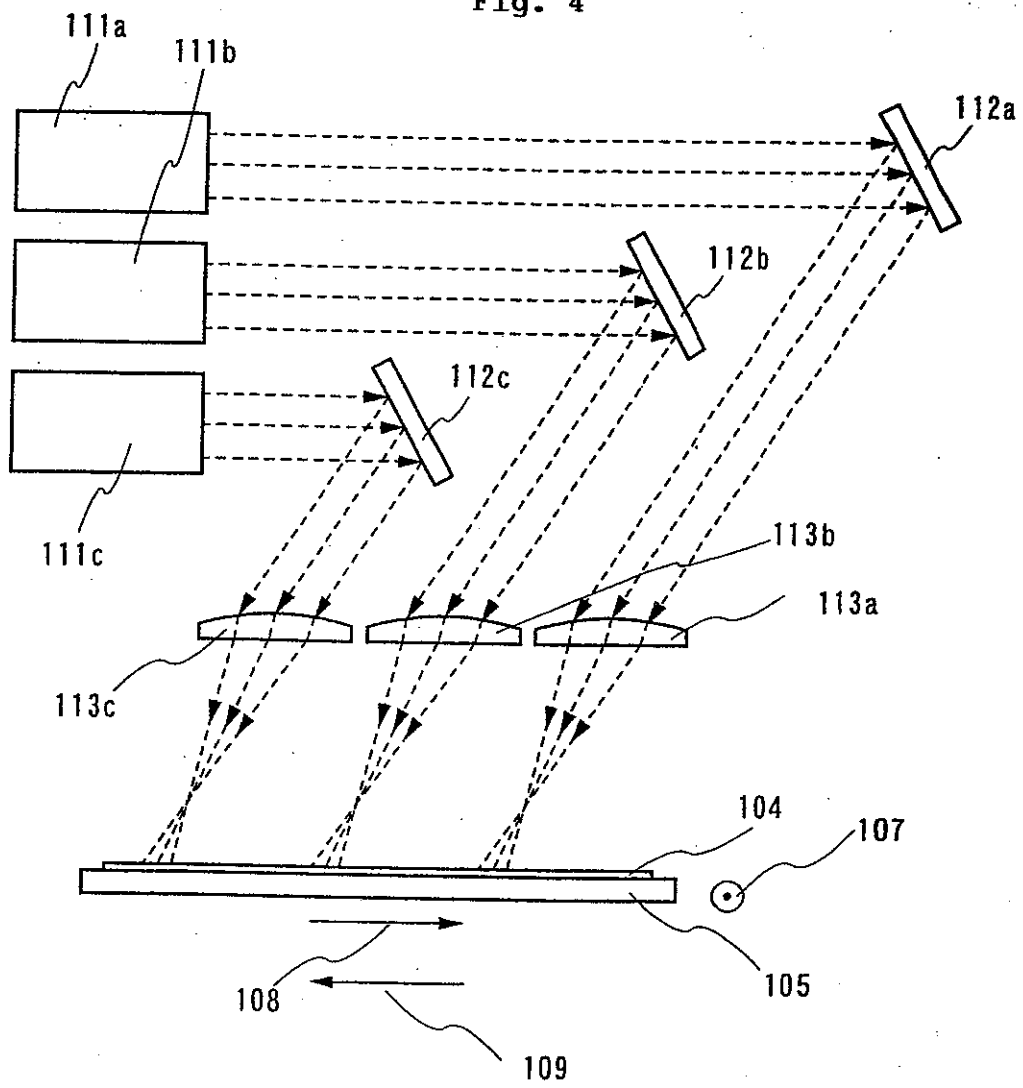


Fig.3

Fig. 4



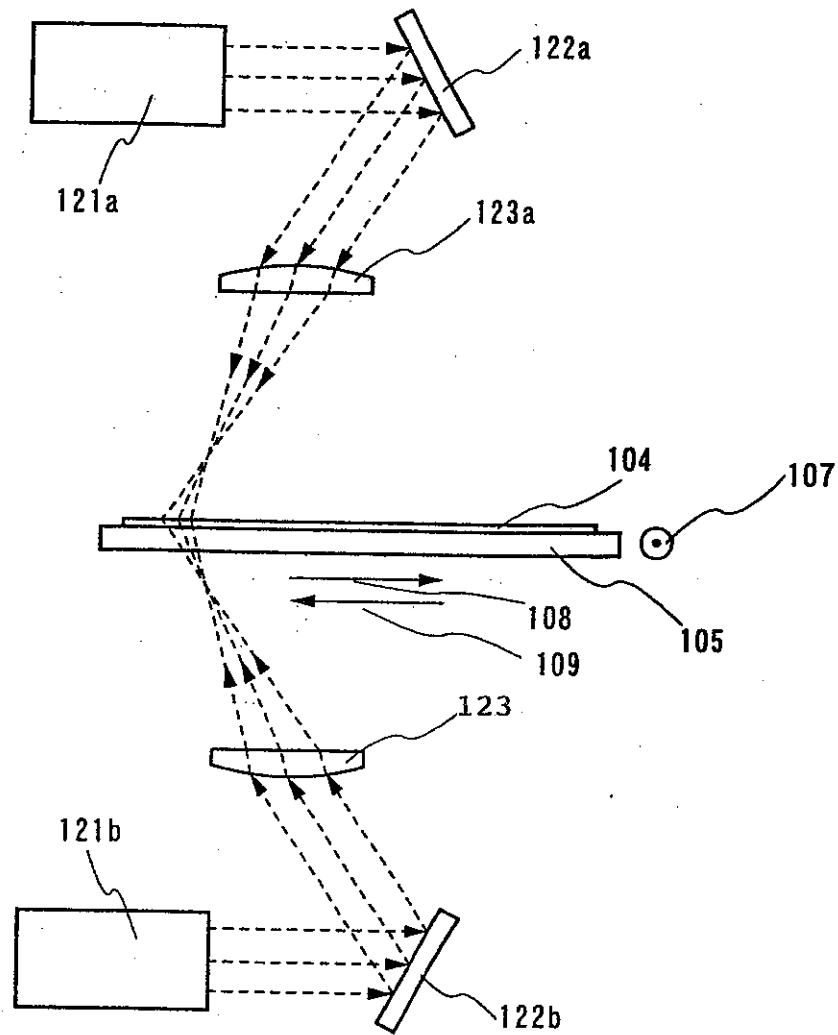


Fig. 5

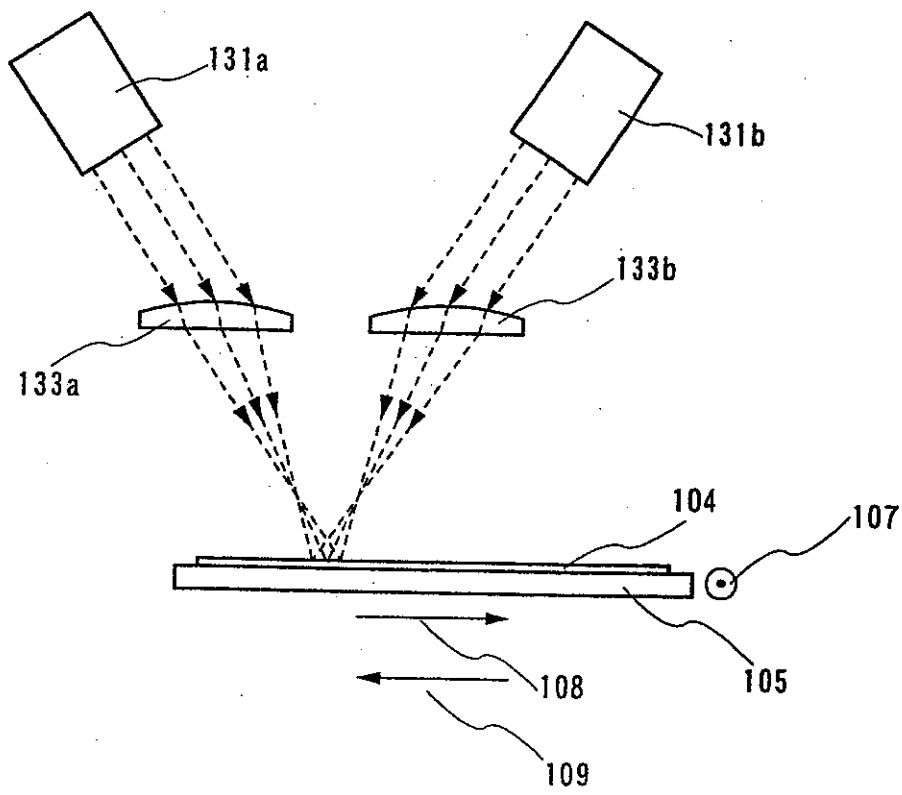


Fig.6

Fig. 7

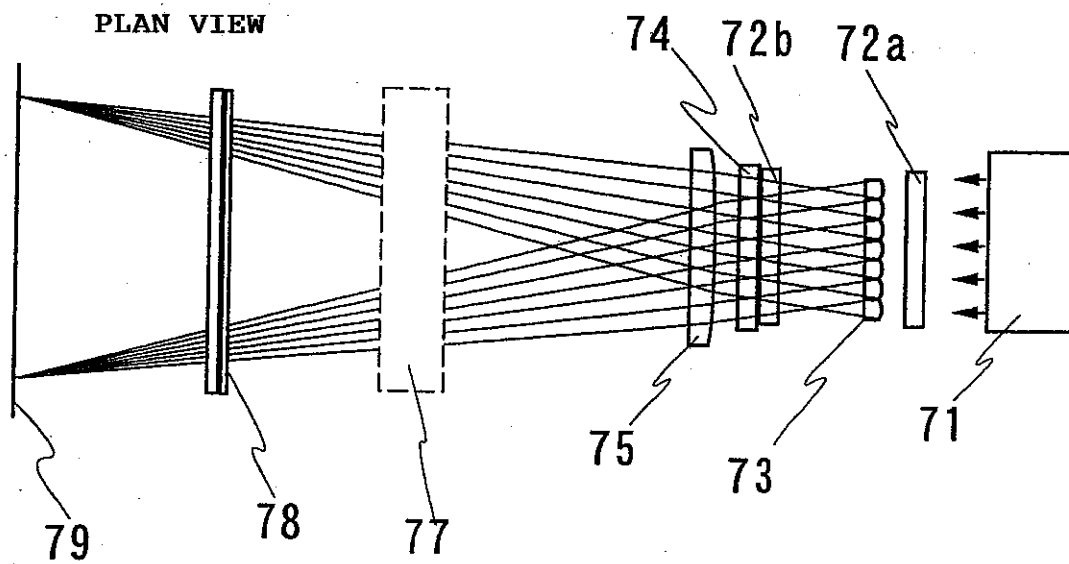
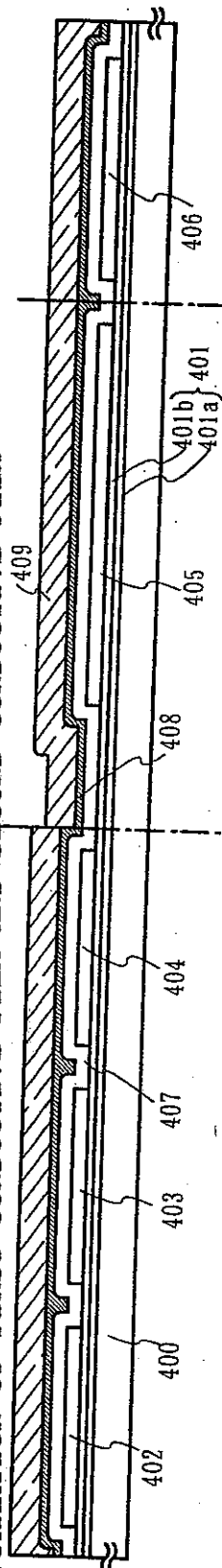
SIDE VIEW

Diagram illustrating the Side View of the optical system. This view shows the axial arrangement of the components and the focusing of light rays. The components are labeled as follows:

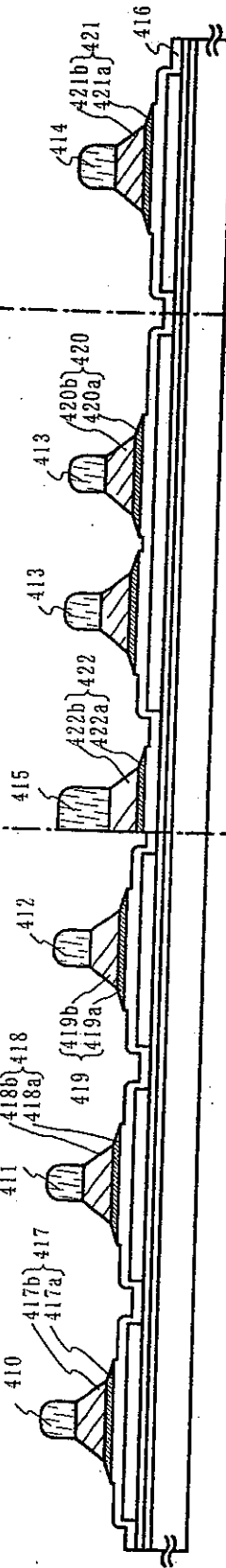
- 77: First lens or aperture.
- 75: Second lens or aperture.
- 74: Third lens or aperture.
- 72b: Fourth lens or aperture.
- 73: Fifth lens or aperture.
- 72a: Sixth lens or aperture.
- 71: Detector or sensor.
- 79: Entrance plane or source.
- 78: First lens or aperture.

Fig. 8A FORMATION OF BASE FILM/FORMATION OF SEMICONDUCTOR LAYER/FORMATION OF INSULATING FILM/
FORMATION OF FIRST CONDUCTIVE FILM AND SECOND CONDUCTIVE FILM



FIRST ETCHING PROCESS

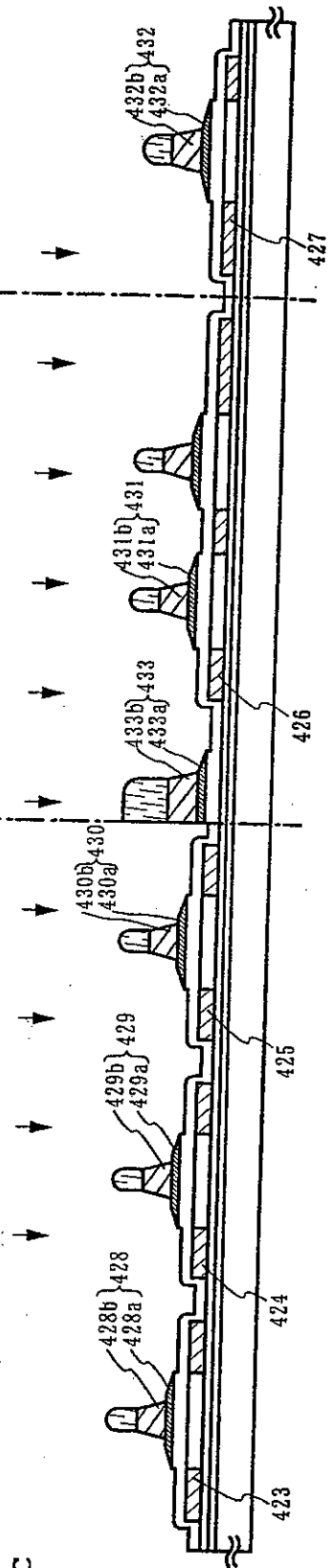
Fig. 8B



SECOND ETCHING PROCESS

FIRST DOPING PROCESS

Fig. 8C



SECOND DOPING PROCESS/THIRD DOPING PROCESS

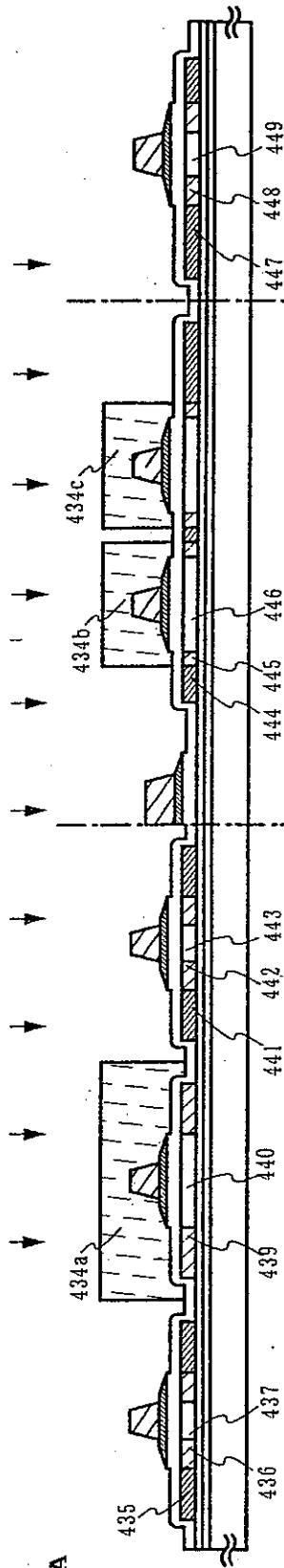


Fig. 9A

FOURTH DOPING PROCESS

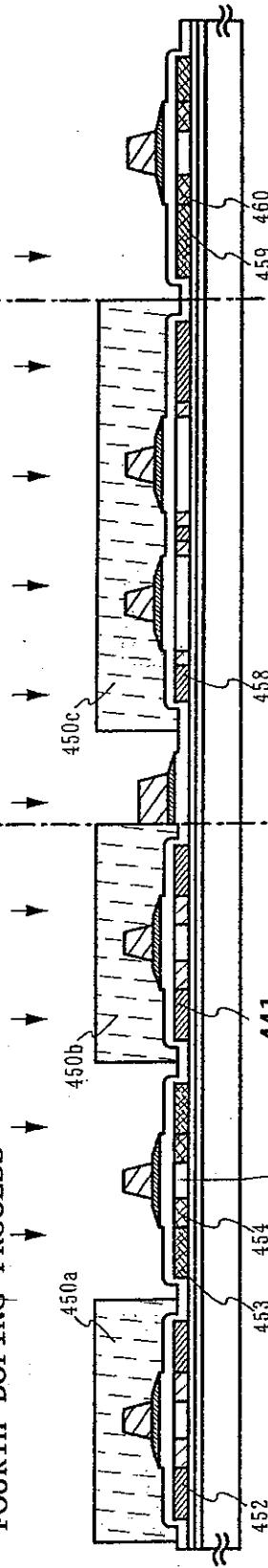


Fig. 9B

FORMATION OF FIRST INTERLAYER INSULATING FILM/LASER BEAM IRRADIATION/HEAT TREATMENT

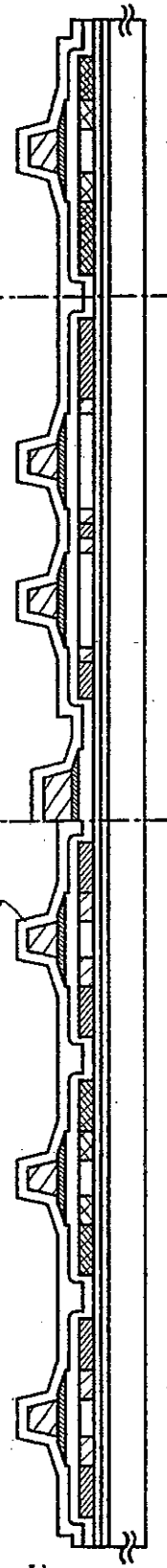


Fig. 9C

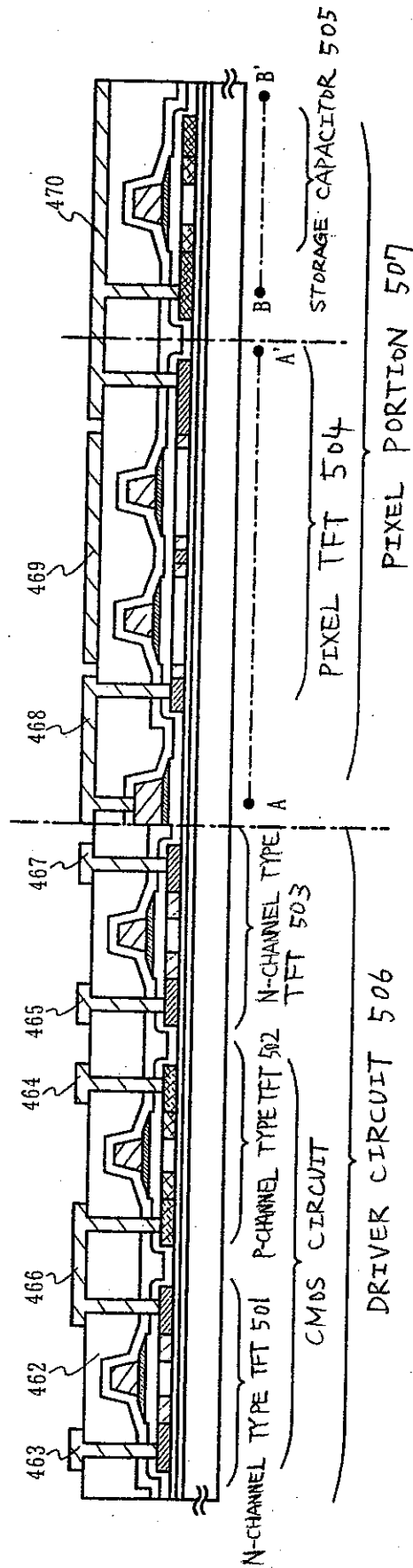
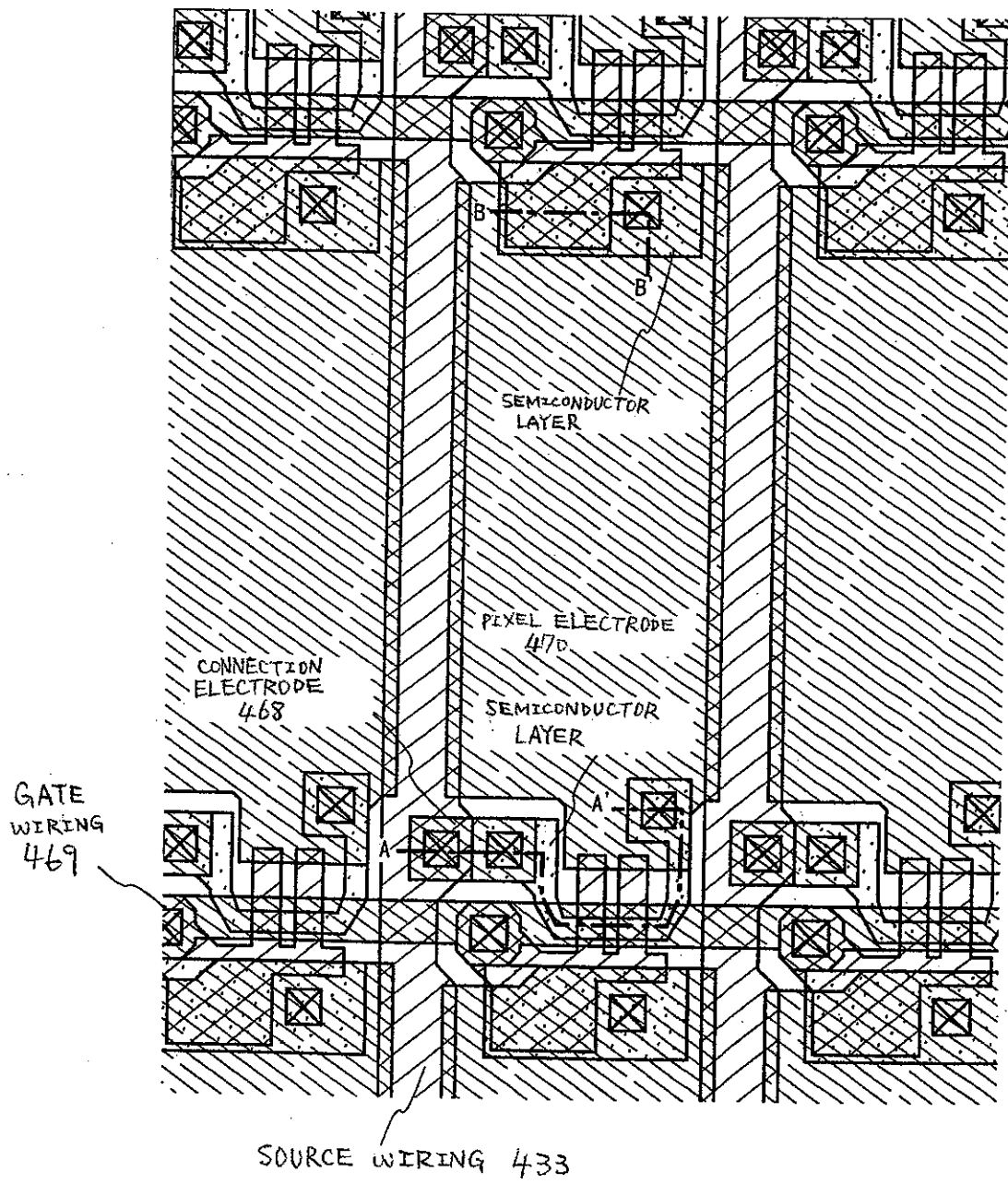


Fig. 10

11/28

Fig. 11



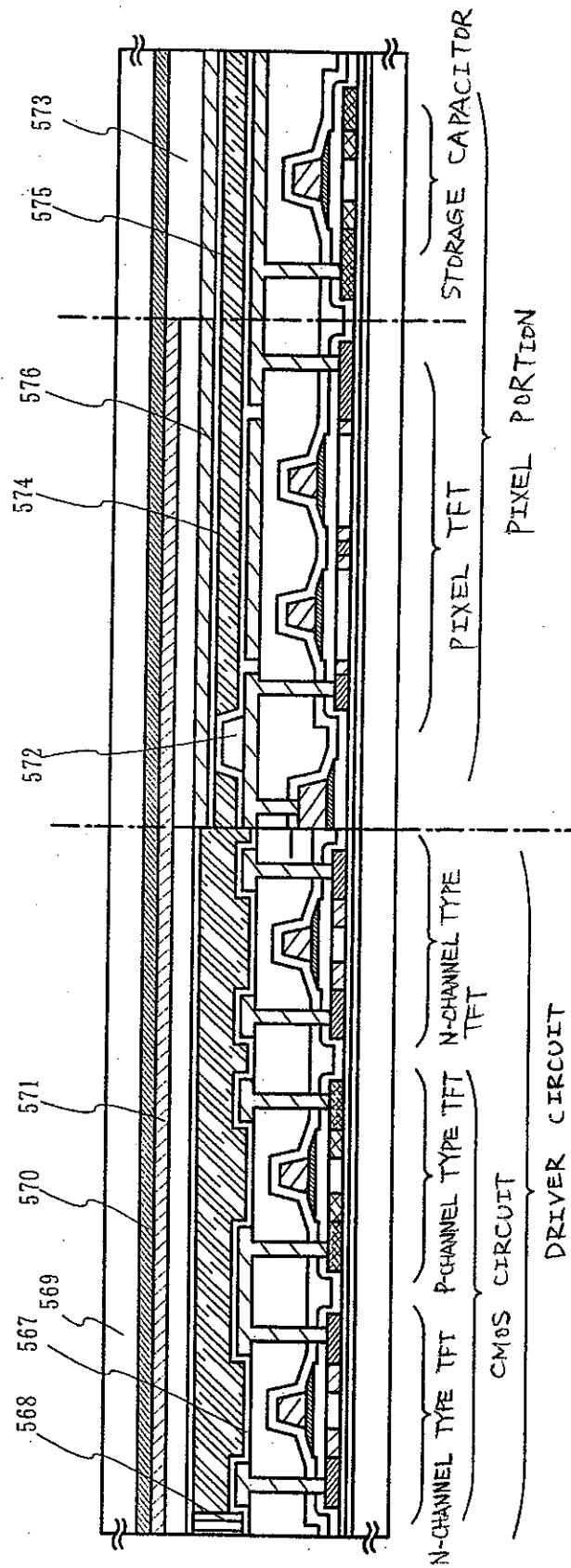


Fig. 12

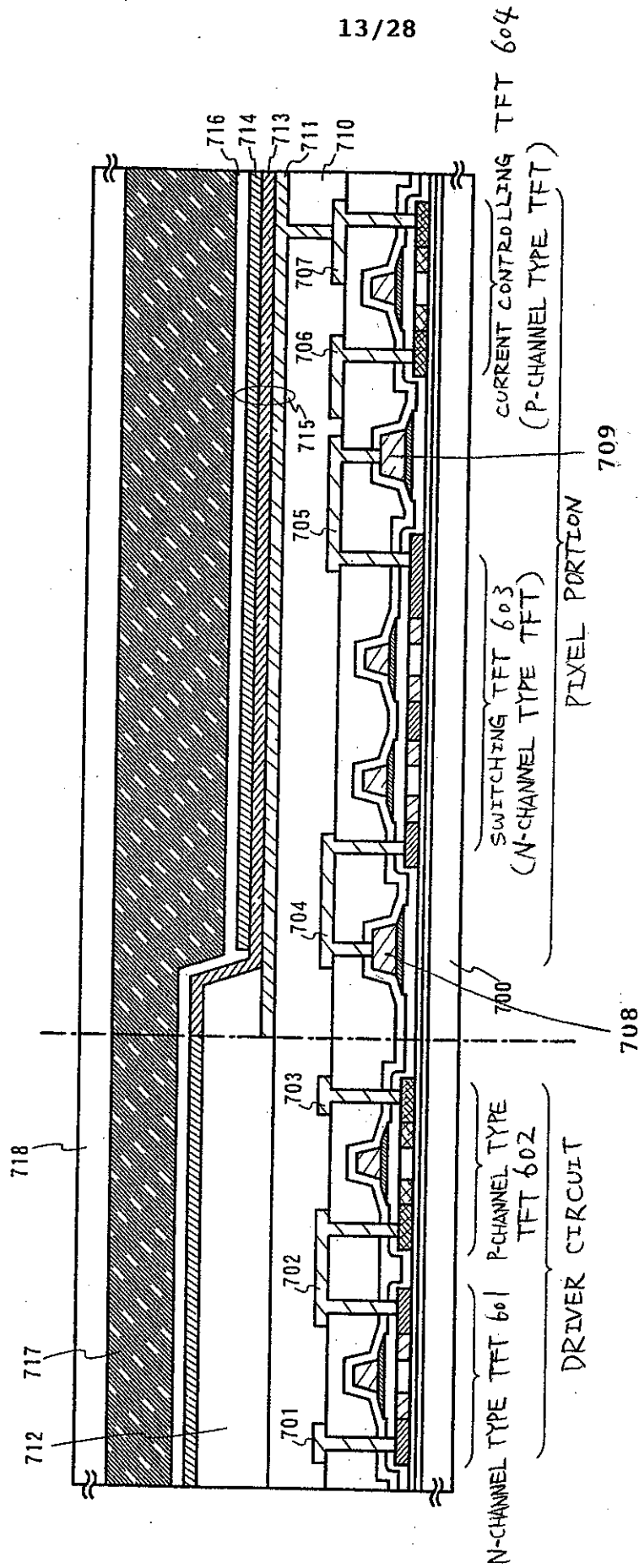
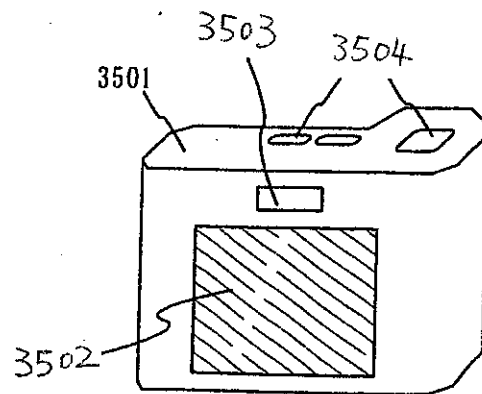
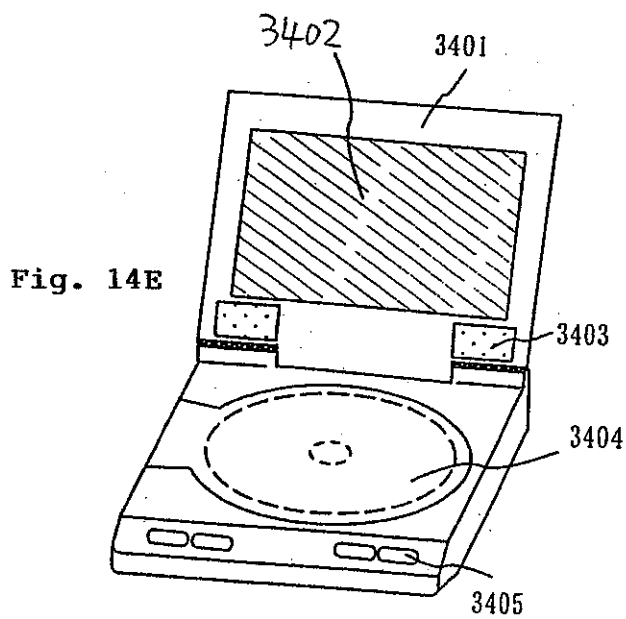
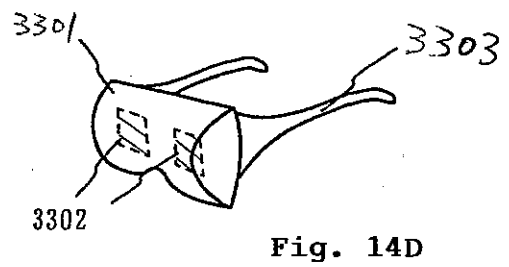
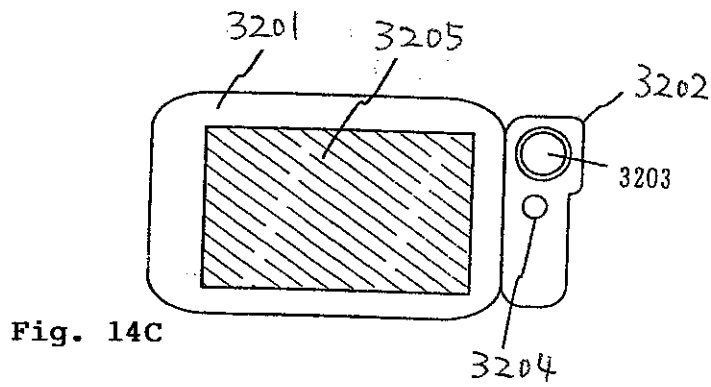
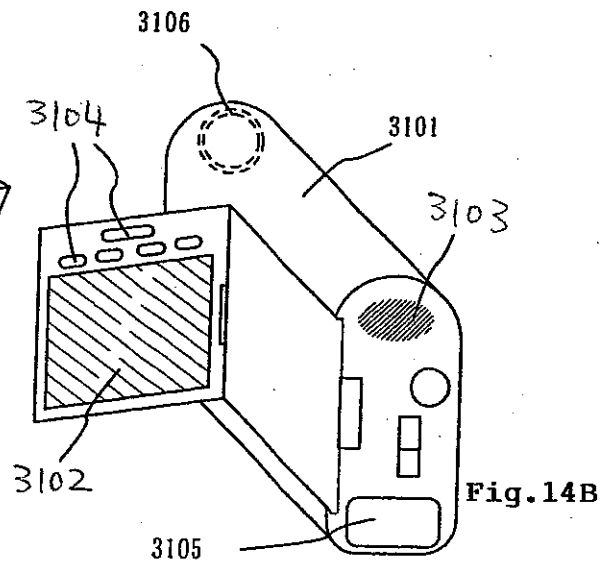
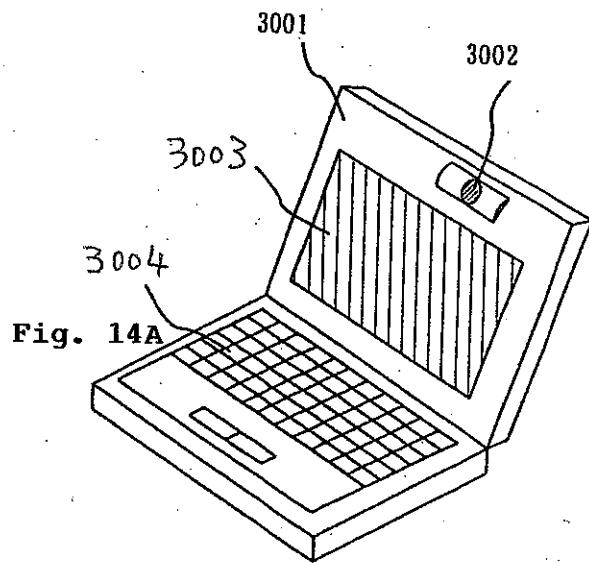
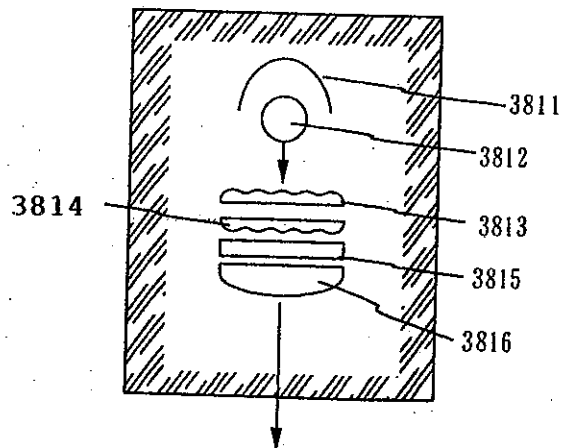
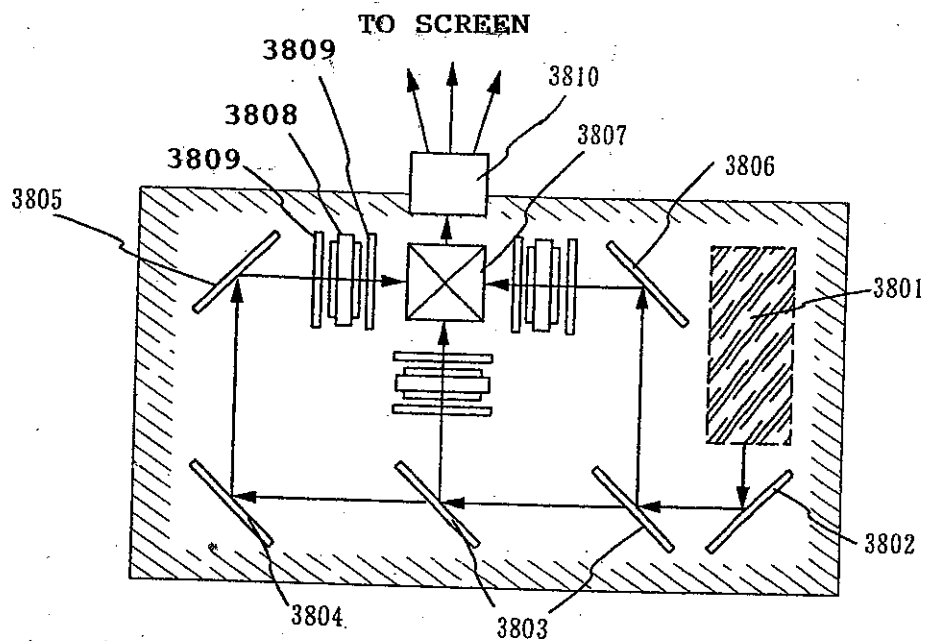
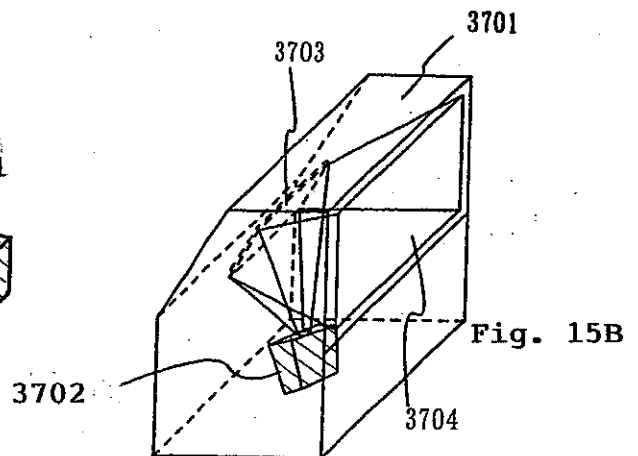
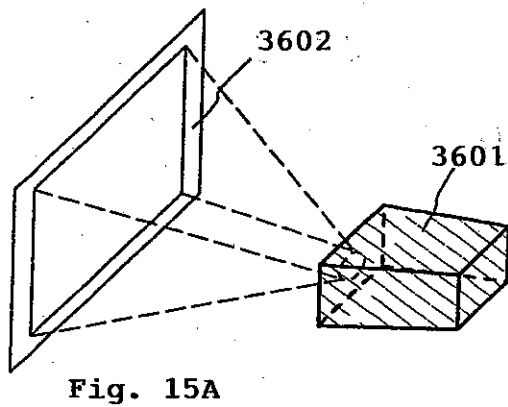
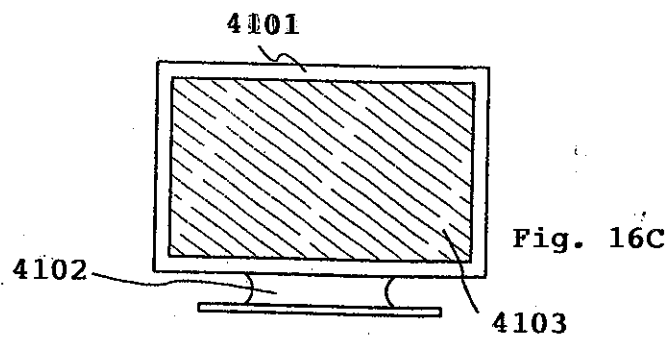
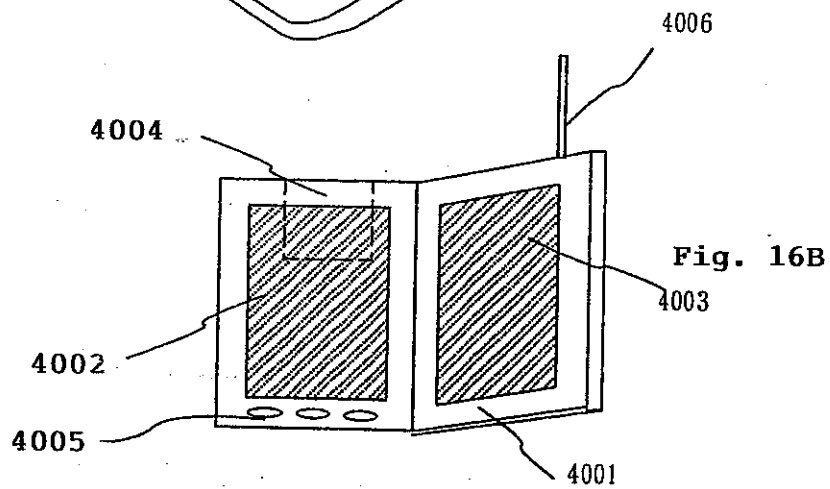
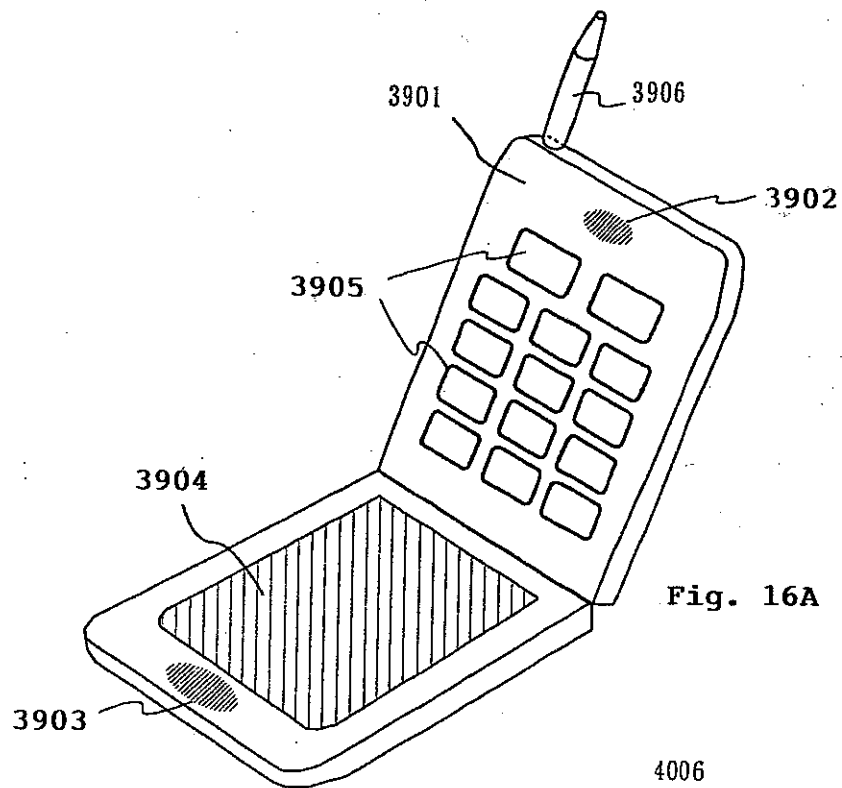


Fig. 13



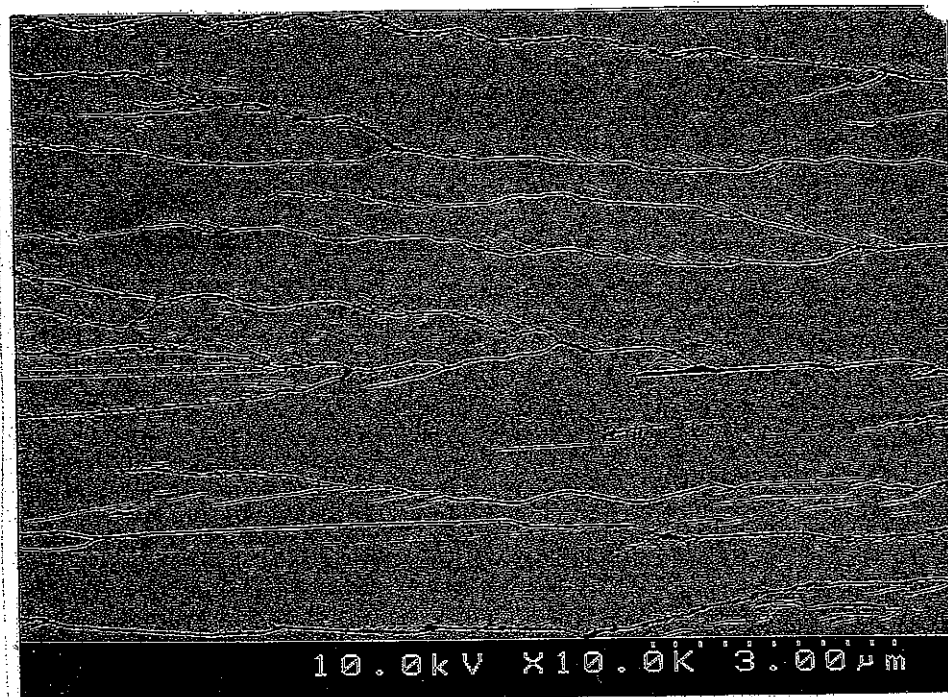






→
RELATIVE SCANNING DIRECTION OF LASER BEAM

Fig.17



→
RELATIVE SCANNING DIRECTION OF LASER BEAM

Fig.18

Fig. 19A FORMATION OF BASE INSULATING FILM /
FORMATION OF SEMICONDUCTOR FILM

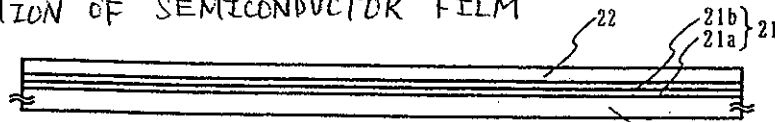


Fig. 19B CRYSTALLIZATION OF SEMICONDUCTOR FILM

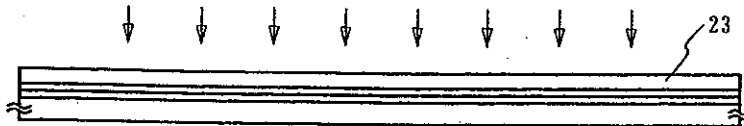


Fig. 19C FIRST DOPING PROCESS



Fig. 19D FIRST ETCHING PROCESS / FORMATION OF INSULATING FILM /
FORMATION OF CONDUCTIVE FILM

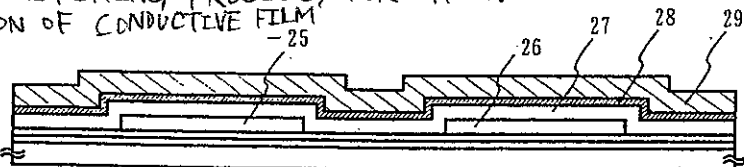


Fig. 19E SECOND ETCHING PROCESS / SECOND DOPING PROCESS

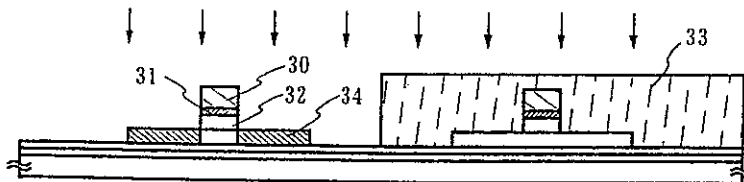


Fig. 19F THIRD DOPING PROCESS

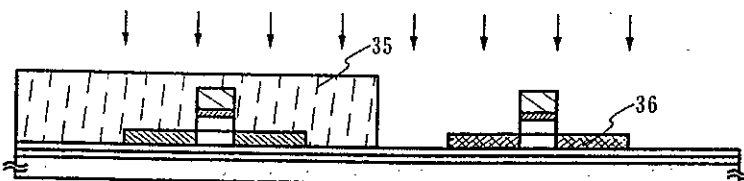
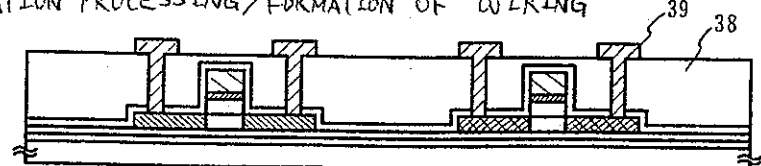


Fig. 19G FORMATION OF FIRST INTERLAYER INSULATING FILM /
HEAT TREATMENT



Fig. 19H FORMATION OF SECOND INTERLAYER INSULATING FILM /
HYDROGENATION PROCESSING / FORMATION OF WIRING



N-CHANNEL TYPE TFT 51

P-CHANNEL TYPE TFT 52

Fig.20A

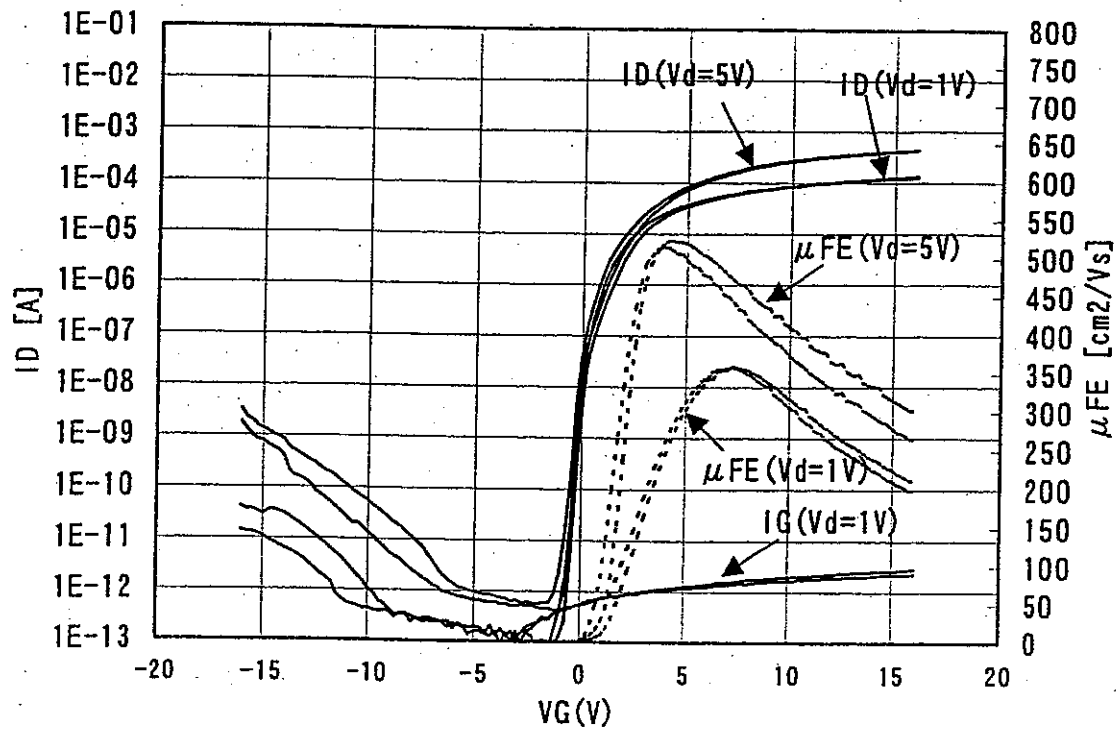
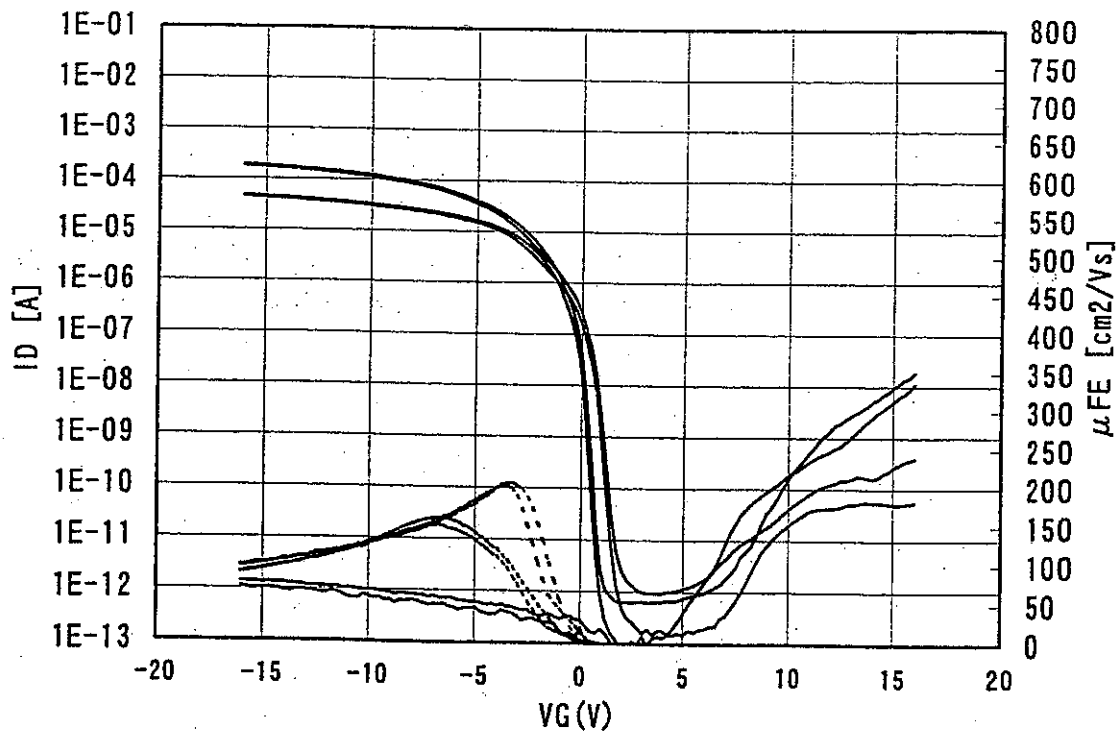


Fig. 20B



FORMATION OF METAL CONTAINING LAYER

Fig. 21A

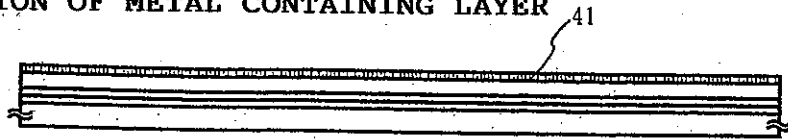


Fig. 21B

HEAT TREATMENT

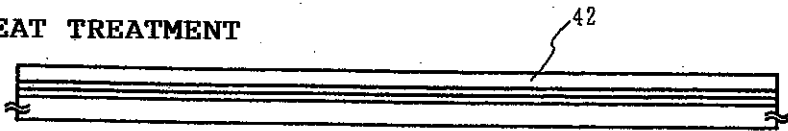


Fig. 21C

LASER ANNEALING



Fig. 22A

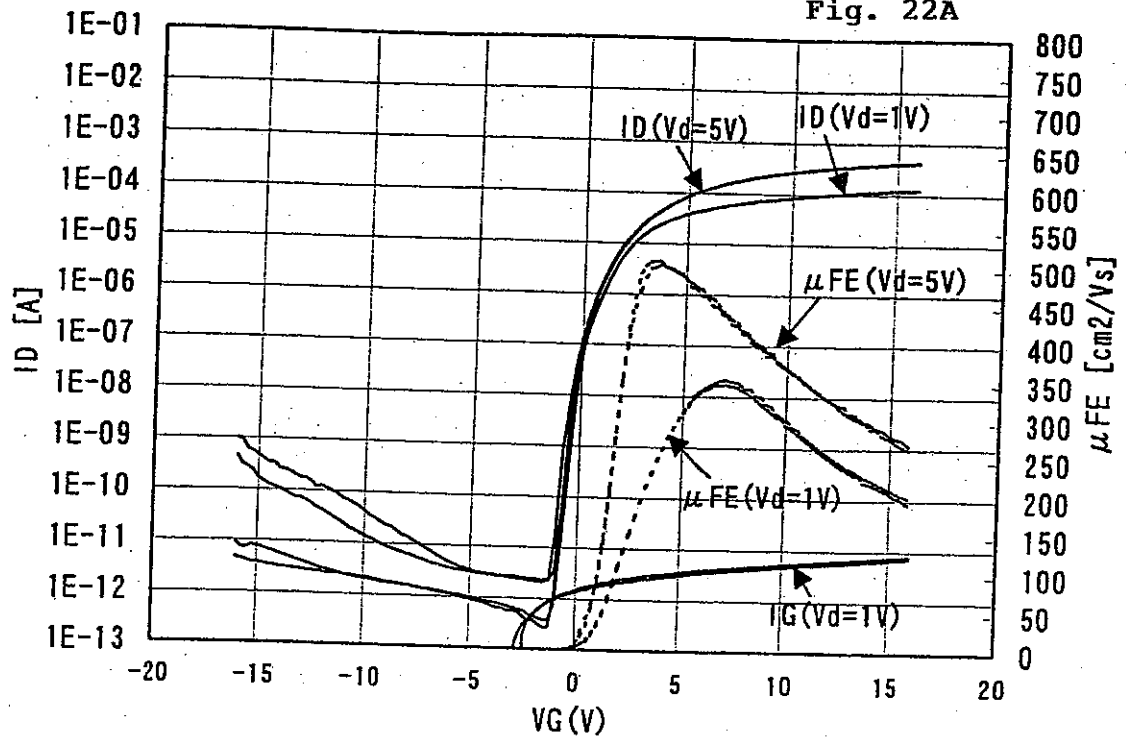


Fig. 22B

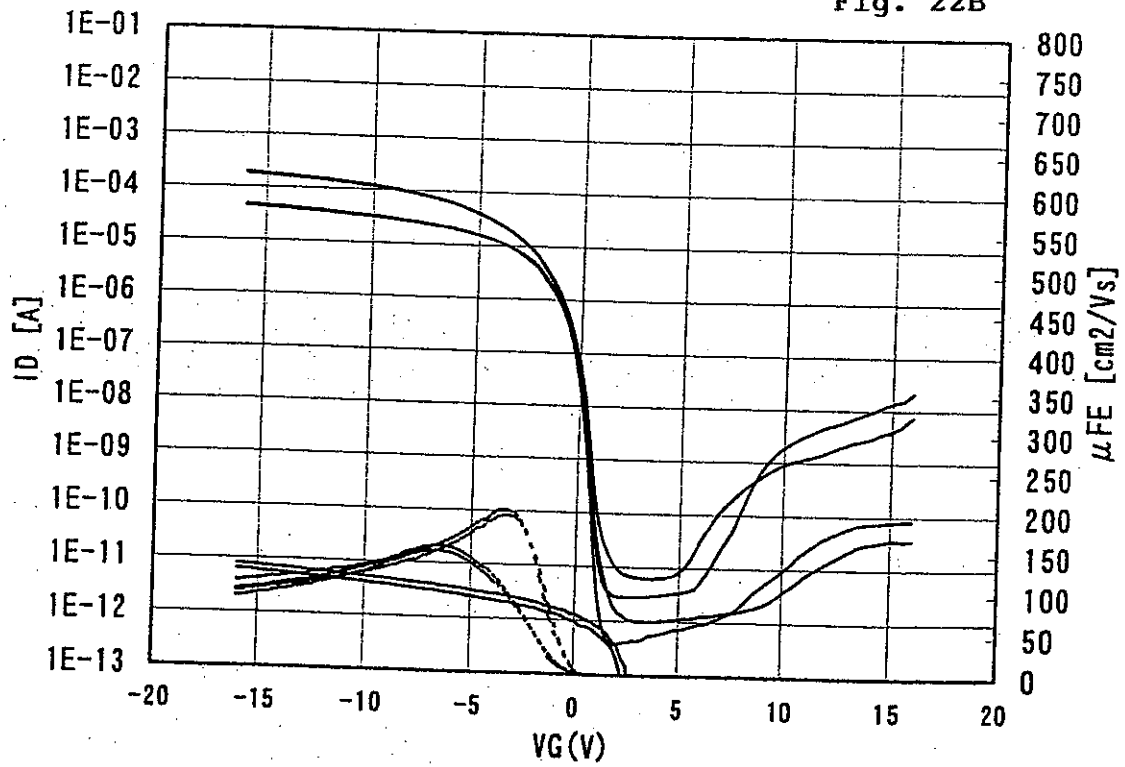


Fig. 23A

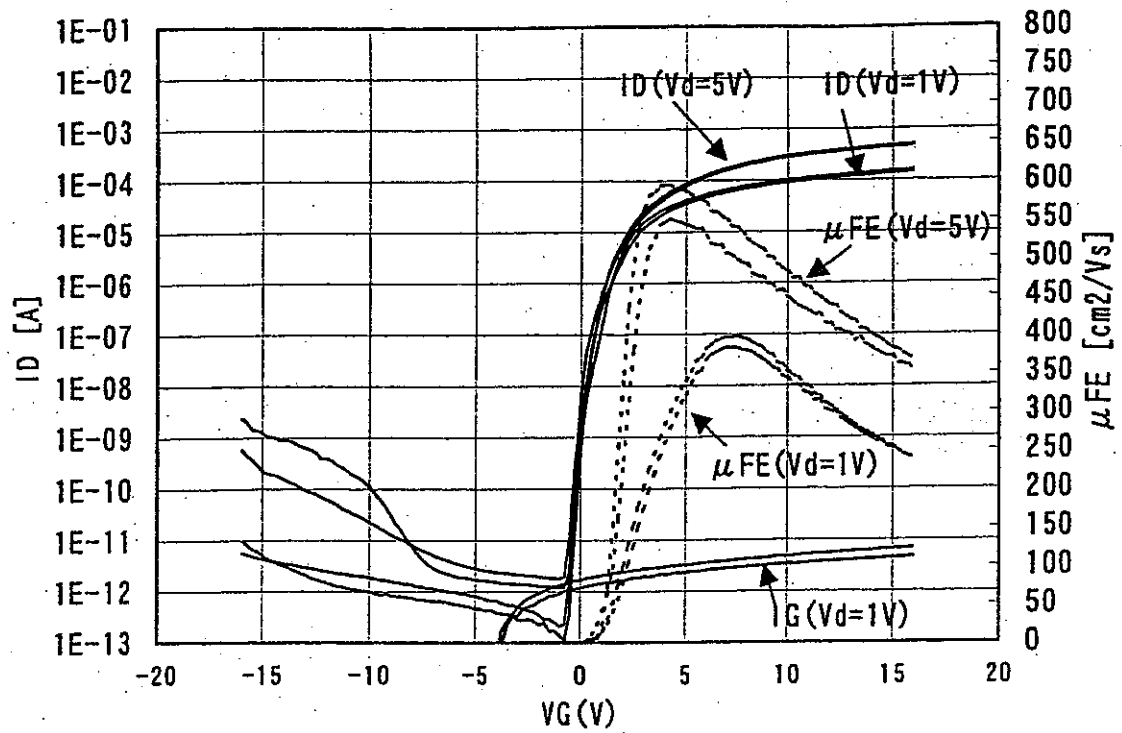
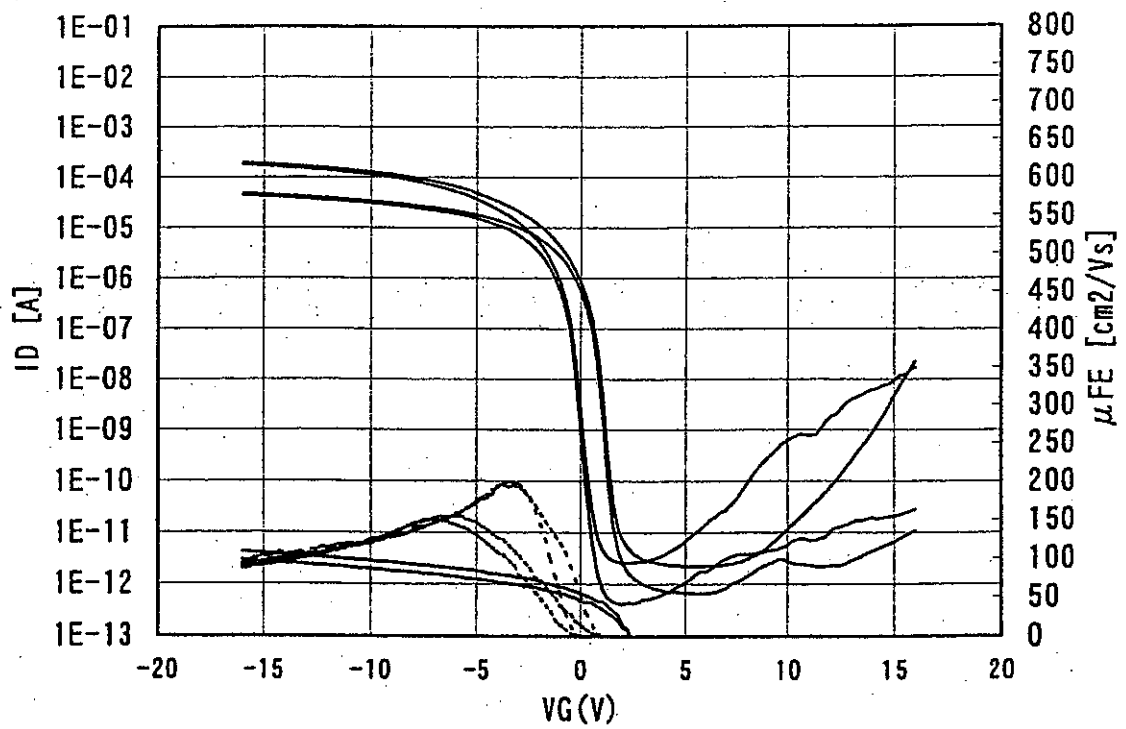


Fig. 23B



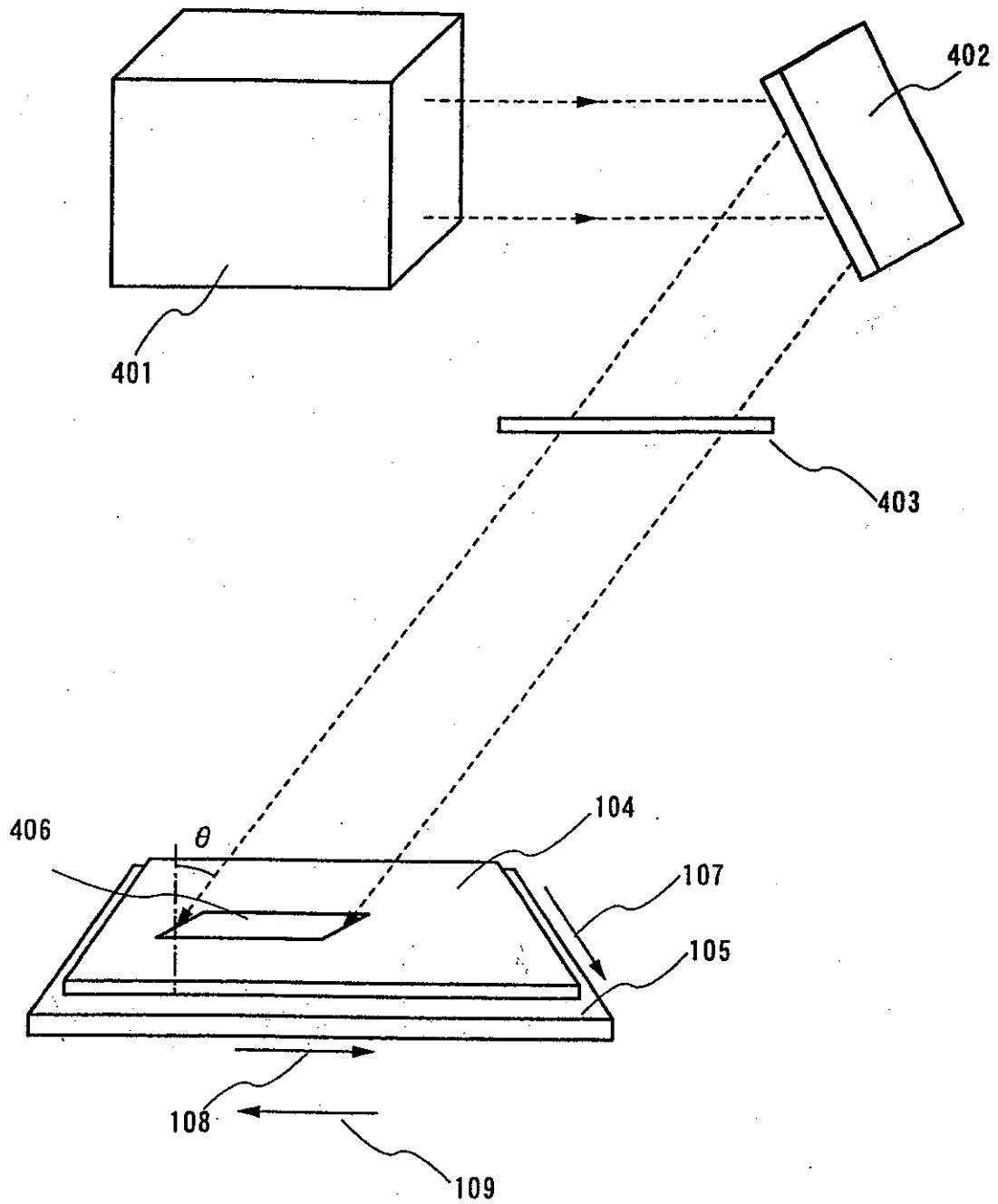


Fig. 24

PG6 N-ch, L/W= 1.5/ 20, Tox= 55

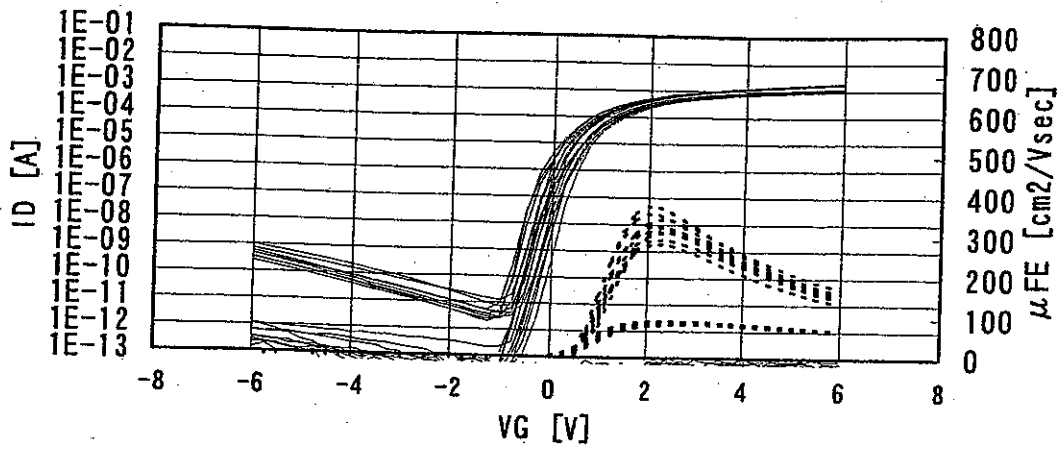


Fig. 25A

PG6 N-ch, L/W= 2/ 20, Tox= 55

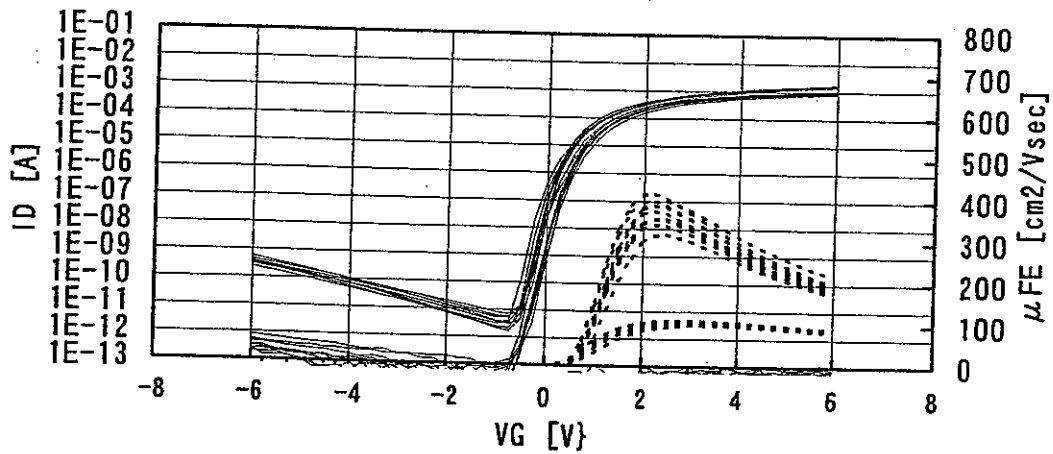


Fig. 25B

PG6 N-ch, L/W= 3/ 20, Tox= 55

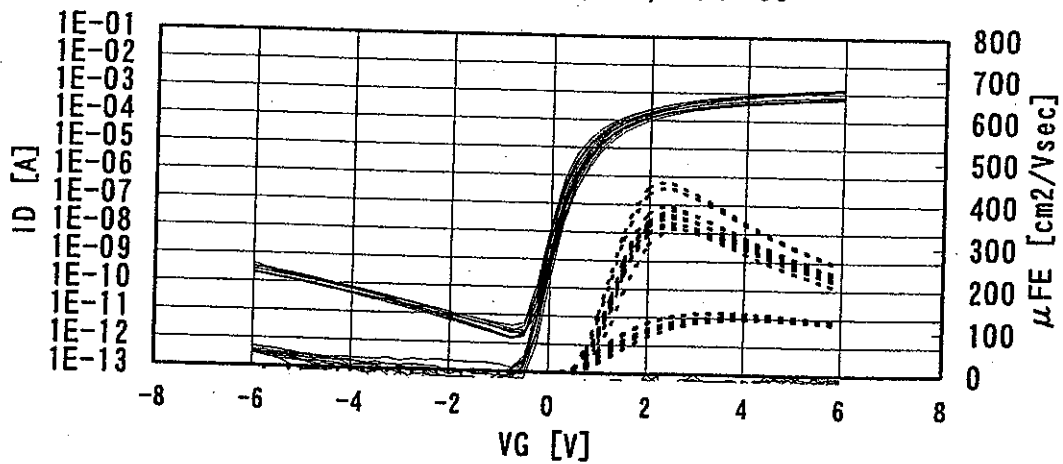
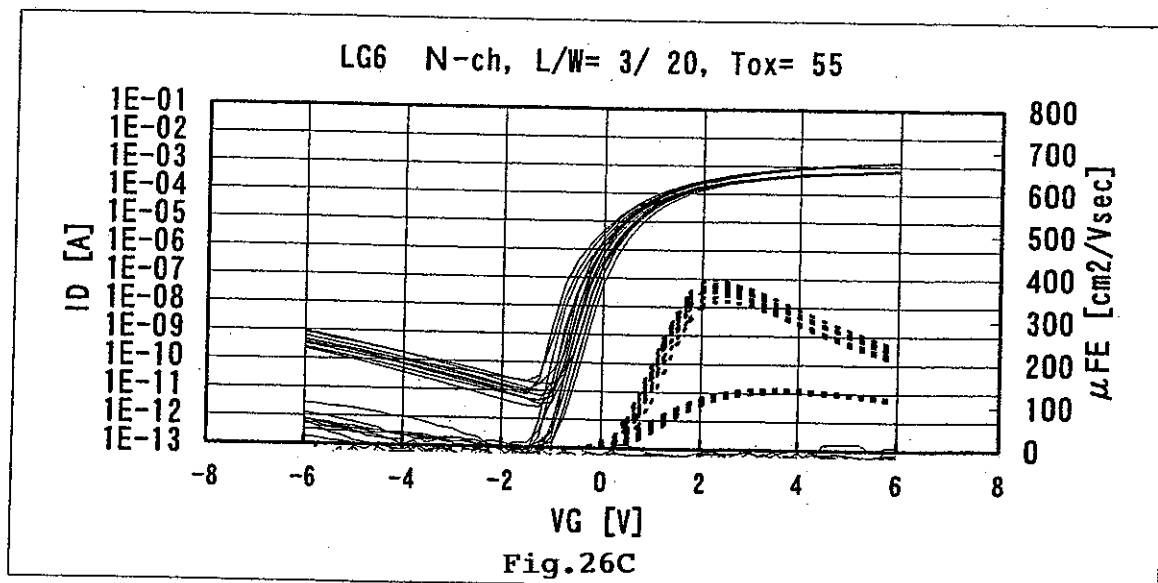
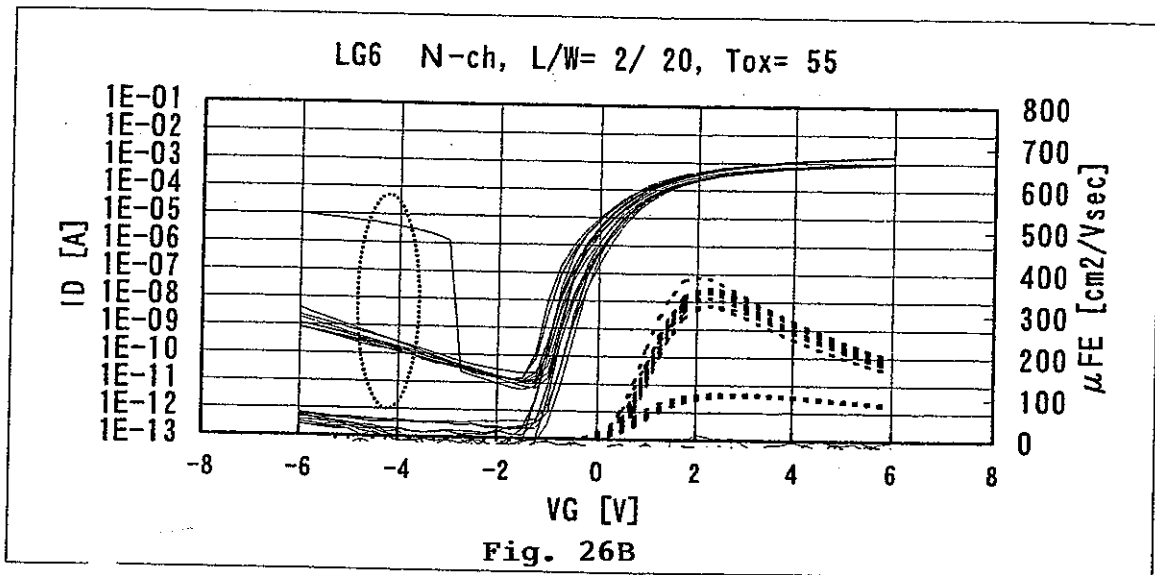
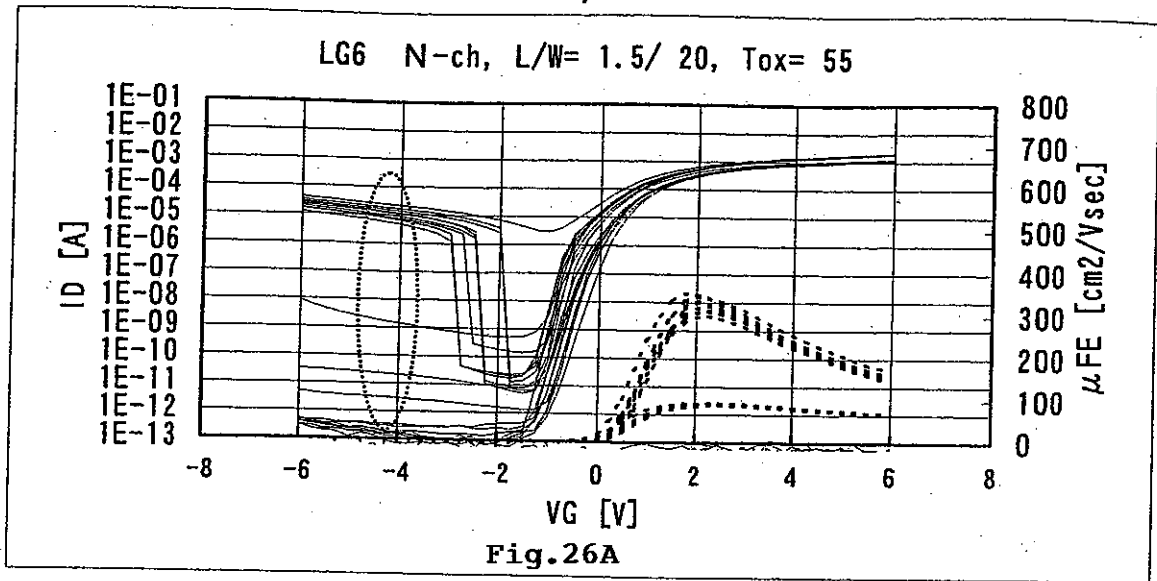


Fig. 25C



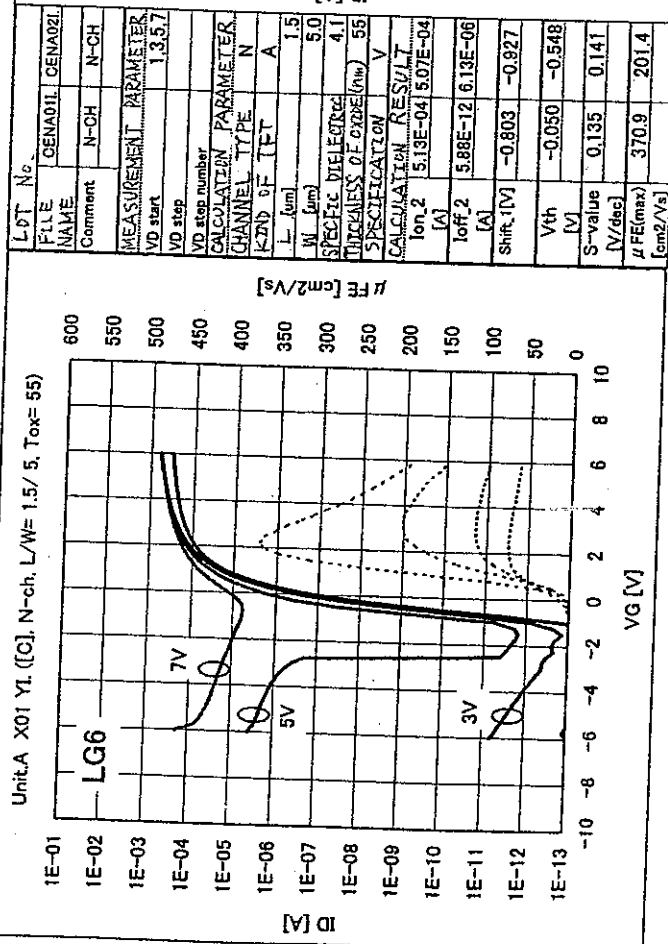
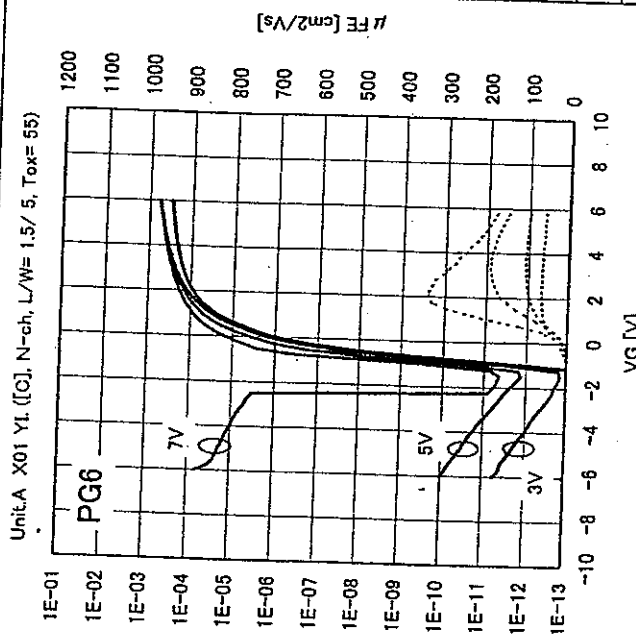
 $L/W=1.25/5\mu\text{m}$

Fig. 27
COMPLETE DEPLETION TYPE (THICKNESS OF SEMICONDUCTOR FILM IS 66nm)

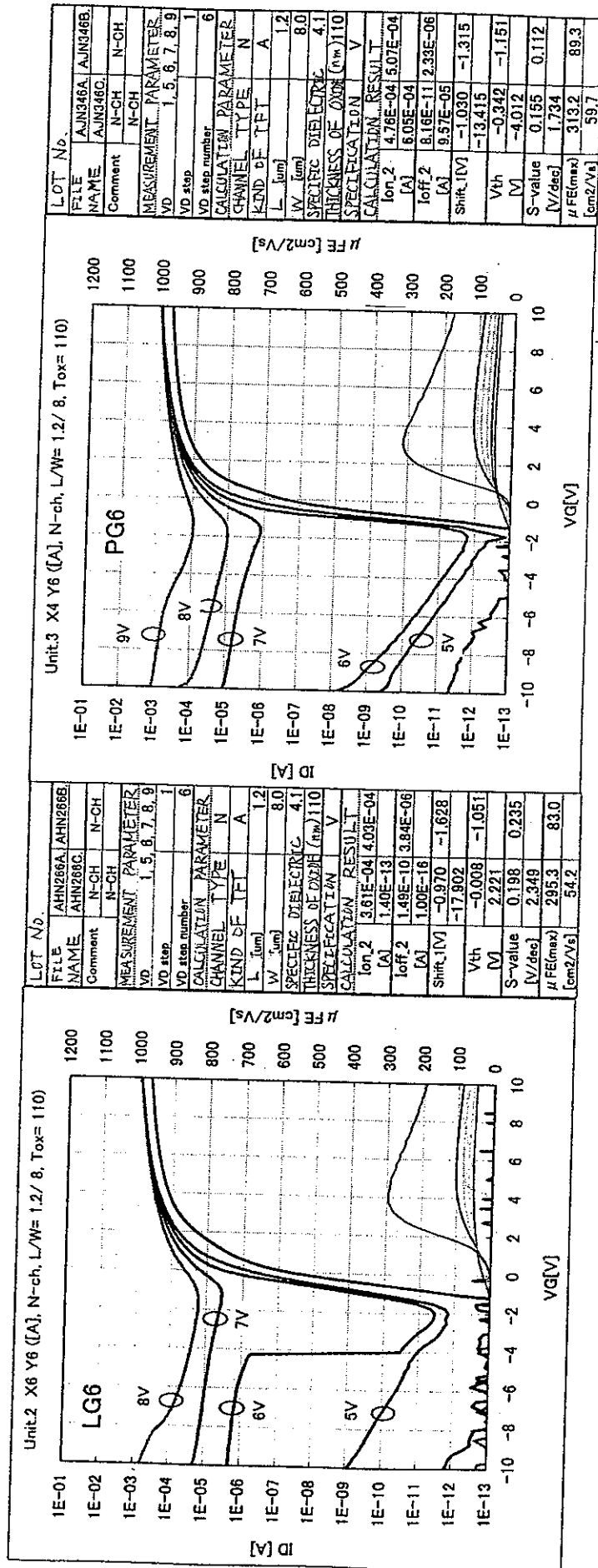


Fig.28

PARTIAL DEPLETION TYPE (THICKNESS OF SEMICONDUCTOR FILM IS 150nm)